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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/799,610	03/15/2004	Makoto Izumi	57810-090	8398	
75	90 07/25/2005		EXAMINER		
McDERMOTT, WILL & EMERY			TRAN, LONG K		
600 13th Street,	N.W. C 20005-3096		ART UNIT PAPER NUMBER		
wasinigion, 2			2818		
			DATE MAILED: 07/25/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	-D
	10/799,610	IZUMI ET AL.	
Office Action Summary	Examiner	Art Unit	
	Long K. Tran	2818	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with t	he correspondence add	ress
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period or - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply y within the statutory minimum of thirty (30 will apply and will expire SIX (6) MONTHS a, cause the application to become ABAND	be timely filed) days will be considered timely, from the mailing date of this con ONED (35 U.S.C. § 133).	nmunication.
Status			
 1) Responsive to communication(s) filed on 28 Jet 2a) This action is FINAL. 2b) This 3) Since this application is in condition for alloware closed in accordance with the practice under E 	s action is non-final. nce except for formal matters		merits is
Disposition of Claims			•
4) ☐ Claim(s) 1 - 21 is/are pending in the applicatio 4a) Of the above claim(s) 9 - 21 is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1 - 8 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.		
Application Papers			
9) ☑ The specification is objected to by the Examine 10) ☐ The drawing(s) filed on is/are: a) ☐ acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	epted or b) objected to by the drawing(s) be held in abeyance. tion is required if the drawing(s) in	See 37 CFR 1.85(a). s objected to. See 37 CFF	
Priority under 35 U.S.C. § 119			
a) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Burear * See the attached detailed Office action for a list	is have been received. Is have been received in Appl rity documents have been rec u (PCT Rule 17.2(a)).	ication No eeived in this National S	Stage
Attachment(s)			
1) X Notice of References Cited (PTO-892)	4) Interview Sumi		
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date <u>3/15/04</u>. 		ail Date nal Patent Application (PTO-	152)

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Election/Restrictions

1. Applicant's election of Group I, claims 1 – 8 in the reply filed on June 28, 2005 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claims **9 – 21** are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a non-elected group there being no allowable generic or linking claim.

Applicant has the right to file a divisional application covering the subject matter of the non-elected claims.

Priority

2. Acknowledgment is made of applicant's claim for foreign priority under 35 U.S.C. 119(a)-(d). The certified copy has been filed on March 15, 2004.

Information Disclosure Statement

3. This office acknowledges of the following items from the Applicant:
Information Disclosure Statement (IDS) filed on March 15, 2004.
The references cited on the PTO -1449 form have been considered.

Specification

- 4. The specification has been checked to the extent necessary to determine the presence of possible minor errors. However, the applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.
- 5. Specification, page 17, line 3: change "electrode 4" to –electrode 5—

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6. Abstract, line 7: change "comprises" to -- includes --.

Claim Rejections - 35 USC § 112

- 7. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 8. Claim 1, the limitations "the minimum limit dimension of lithography" is unclear. The minimum limit dimension of the lithography will change over time depending on the improvements in processes and apparatus. For examination purposes, the minimum limit dimension of the lithography is considered higher than 100 nm (as described in the applicant's specification page 17, line 20 22).

Claim Rejections - 35 USC § 102

9. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 10. Claims 1, 2 are rejected under 35 U.S.C. 102(b) as being anticipated by Hawkins et al. (US Patent No. 5,719,075).
- 11. Regarding claim 1, Hawkins discloses a solid state image device comprising: a gate insulator film 20 (figs. 2B 2M; column 6, lines 54 64) formed on a semiconductor substrate 10 (figs. 2A 2M); a first gate electrode 30a (figs. 2B 2M; column 6, lines 64 67 and column 7, lines 11 15), formed on said gate insulator film 20, having a substantially flat upper surface 31 (fig. 2F; column 8, lines 7 25 and lines 39 44); and a second gate electrode 40a (figs. 2E 2M; column 8, lines 7 10)

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formed on said gate insulator film 20 through an insulator film 48 (figs. 2D - 2M; column 7, lines 42 - 50), having a thickness, in range from 200 to 1000 Å, smaller than the minimum limit dimension of lithography to be adjacent to said first gate electrode 30a without overlapping said first gate electrode 30a.

Regarding claim 2, Hawkins discloses the insulator film 48 including a thermal oxide, silicon dioxide, film (column 7, lines 42 - 47).

Regarding claim 3, Hawkins discloses the second gate electrode 40a has a substantially flat upper surface 41(fig. 2F; column 8, lines 7 - 25 and lines 39 - 44)

Regarding claim **4**, Hawkins discloses the upper surfaces 31 and 41of said first gate electrode 30a and said second gate electrode 40a are substantially flush with each other (fig. 2F; column 8, lines 12 – 44).

Regarding claim **5**, Hawkins discloses the upper surface of said insulator film 48 is substantially flush with the upper surfaces of said first gate electrode 30a and said second gate electrode 40a (fig. 2F; column 8, lines 12 – 44. Note coplanar within 100 Å is considered substantially flush for CMP process (column 8, line 13 – 14 and lines 40 – 44); many possible planarizing procedures (column 8, lines 17 - 18) can be used to improve the coplanar.

Regarding claim **6**, Hawkins discloses the gate insulator film 20 including silicon nitride insulator film 16 (fig. 2A) at least partially having an oxidation inhibiting function. (Note although Hawkins does not explicitly teach film 16 at least partially having an oxidation inhibiting function. However, since the insulator layer 16 of Hawkins and the insulator film 20b of the claimed invention is made of the same material therefore, it is

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inherent that the insulator 16 of Hawkins having at least partially having an oxidation inhibiting function as claimed invention).

Regarding claim 7, Hawkins discloses the gate insulator film 20 includes a first gate insulator film 14 (fig. 2A) and a second gate insulator film 16 (fig. 2A) formed on the first gate insulator film.

Regarding claim **8**, Hawkins discloses the insulator film **14** (fig. 2A) is a silicon dioxide layer (column 6, line 57 – 59).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Long K. Tran whose telephone number is 571-272-1797. The examiner can normally be reached on Mon-Thu.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LKT July 6, 2005

WRM